

Description

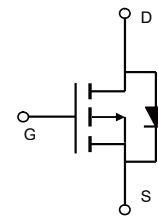
The VSM82P06 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This device is well suited for high current load applications.

General Features

- $V_{DS} = -60V, I_D = -82A$
 $R_{DS(ON)} < 13m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 16m\Omega @ V_{GS} = -4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Load switch



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM82P06	VSM82P06-TC	TO-220	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-82	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D (100^\circ C)$	-58	A
Pulsed Drain Current	I_{DM}	-328	A
Maximum Power Dissipation	P_D	150	W
Derating factor		1.0	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	722	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.0	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

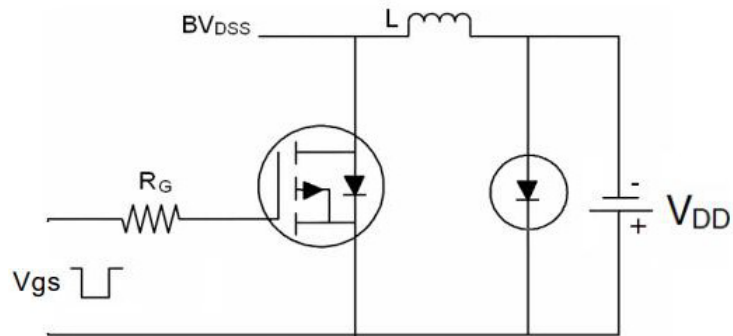
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.2	-1.8	-2.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	11	13	mΩ
		V _{GS} =-4.5V, I _D =-20A	-	13	16	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	-	25	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-30V, V _{GS} =0V, F=1.0MHz	-	5604	-	PF
Output Capacitance	C _{oss}		-	356	-	PF
Reverse Transfer Capacitance	C _{rss}		-	265	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-30V, R _L =1.5Ω, V _{GS} =-10V, R _G =3Ω	-	18	-	nS
Turn-on Rise Time	t _r		-	20	-	nS
Turn-Off Delay Time	t _{d(off)}		-	55	-	nS
Turn-Off Fall Time	t _f		-	35	-	nS
Total Gate Charge	Q _g	V _{DS} =-30, I _D =-20A, V _{GS} =-10V	-	62.1		nC
Gate-Source Charge	Q _{gs}		-	9.3		nC
Gate-Drain Charge	Q _{gd}		-	16.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-20A	-		-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-82	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A di/dt = -100A/μs ^(Note3)	-	49		nS
Reverse Recovery Charge	Q _{rr}		-	71		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

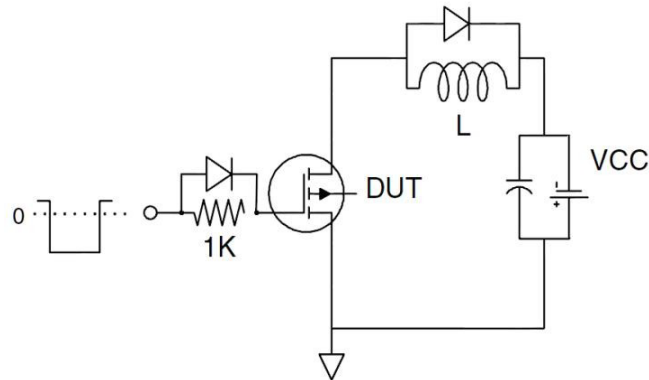
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^{\circ}\text{C}, V_{DD}=-30V, V_G=-10V, L=0.5mH, R_G=25\Omega$

Test Circuit

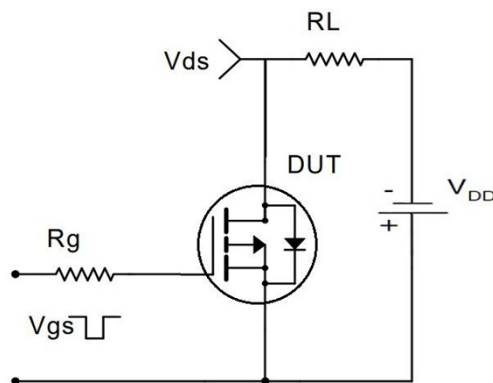
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

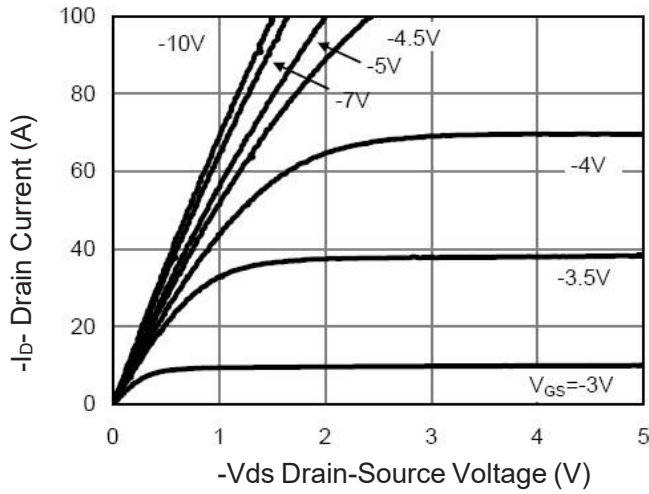


Figure 1 Output Characteristics

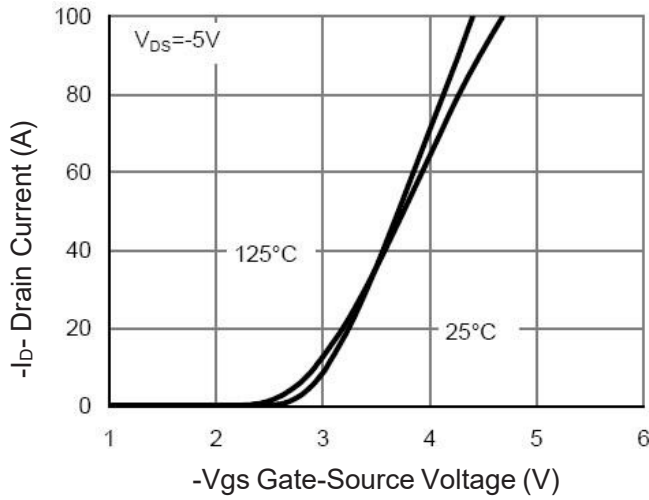


Figure 2 Transfer Characteristics

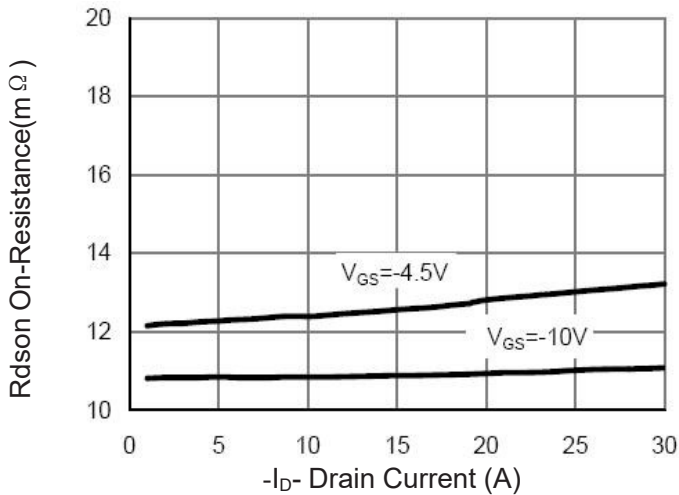


Figure 3 Rdson- Drain Current

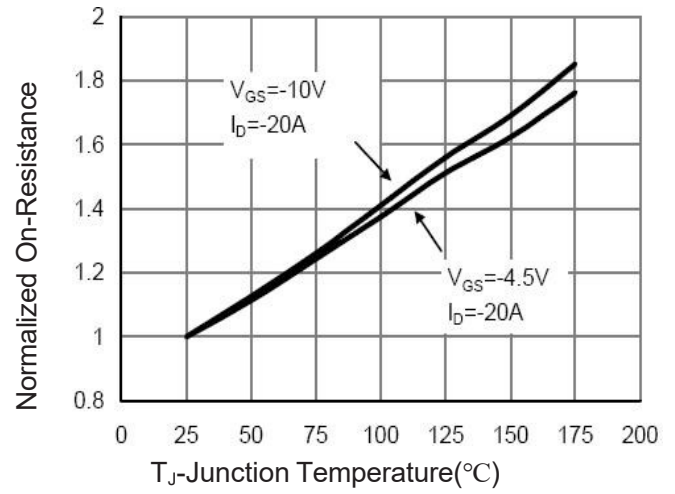


Figure 4 Rdson-Junction Temperature

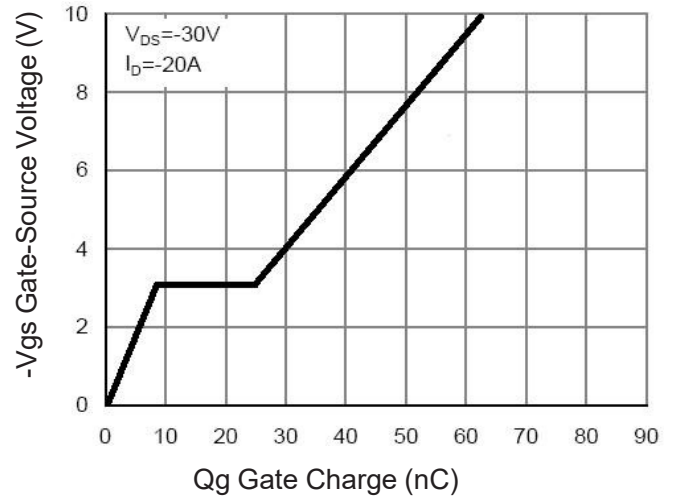


Figure 5 Gate Charge

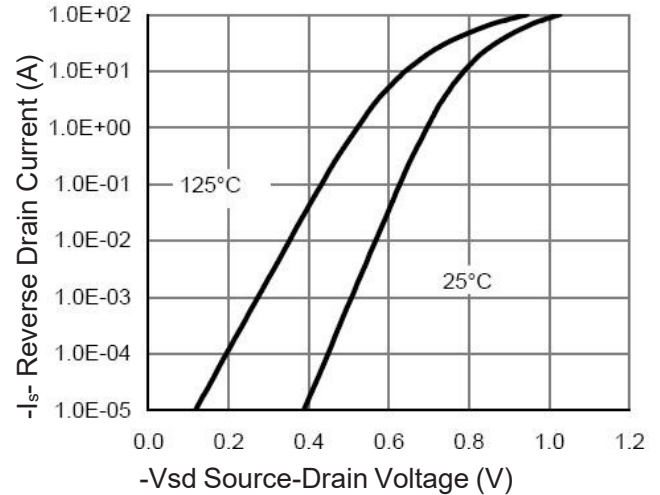
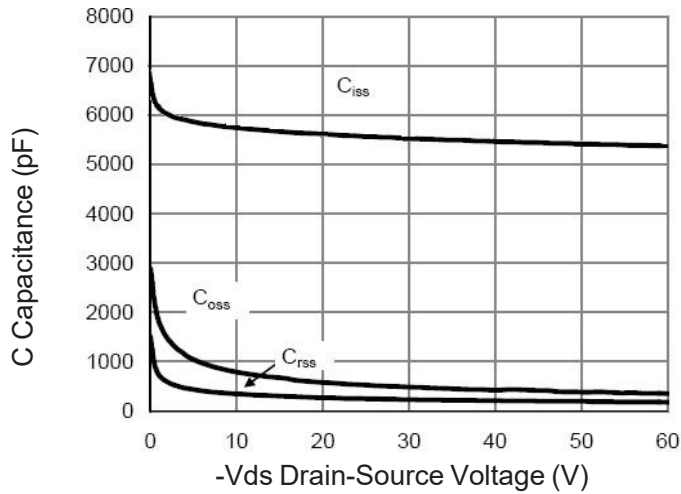
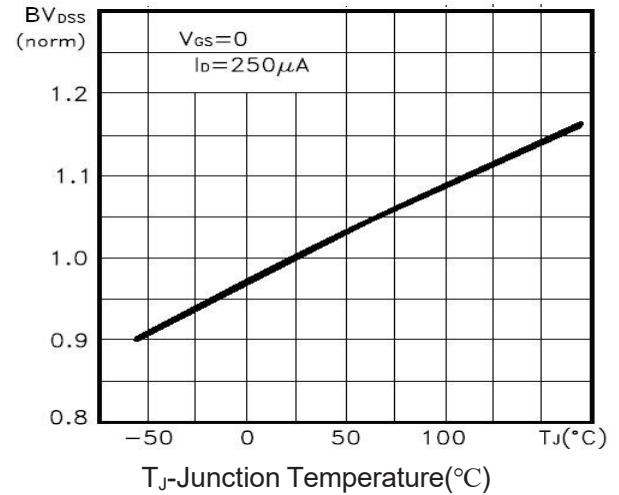
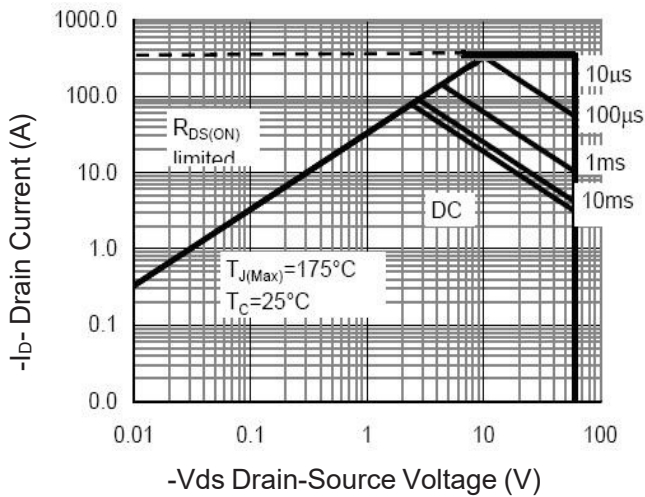
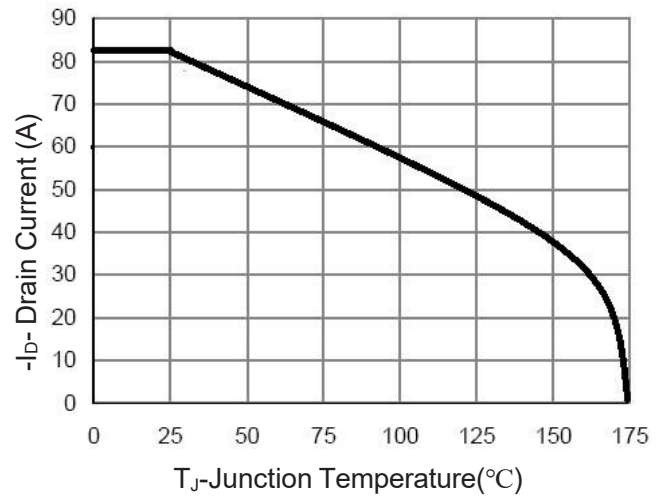
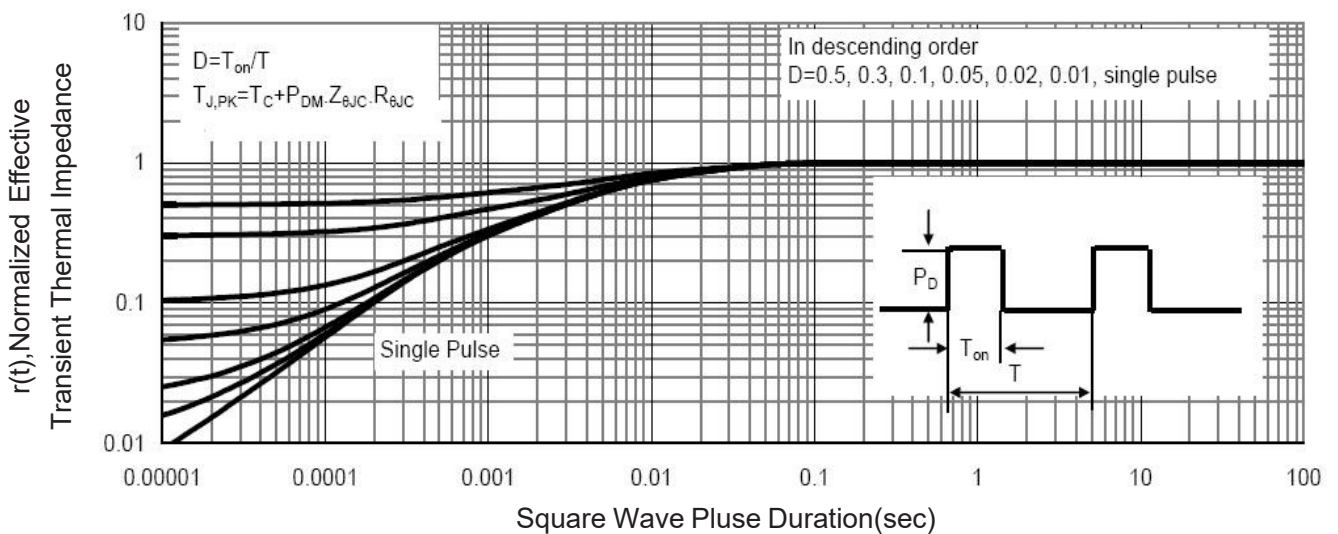


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature

Figure 8 Safe Operation Area

Figure 10 I_D Current Derating vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance